

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

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PATENT & TRADEMARK OFFICE

ATTY DOCKET NO.
SETI-0002

SERIAL NO.
09/966,559

Khan et al.

FILING
09/27/2001

GROUP
2818

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TL		"DC, Microwave, and High-Temperature Characteristics of GaN FET Structures," S. C. Binari et al., Inst. Phys. Conf. Ser. No. 141: Chapter 4, Presented at Int. Symp. Compound Semicond., San Diego, CA, Sept. 18-22, 1994, pp. 459-462.
TL		"GaN - AlxGa1-xN Heterostructures Deposition by Low Pressure Metalorganic Chemical Vapor Deposition For Metal Insulator Semiconductor Field Effect Transistor (MISFET) Devices," M. Khan et al., Material Research Society Symposium Proceedings Vol. 281 (1993), pp.769-774.

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2/8/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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SERIAL NO. 09/966,559

Khan et al.

FILING

09/27/2001

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2818


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[illegible]

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			<p>"Low Dark Current Transparent Schottky Barrier UV Detectors," G. Simin et al., ICNS3, Montpellier, June 1999.</p>

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INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)

SETI-006

Application Number

09/966559

Applicant(s)

Khan et al.

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9/27/2001

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2818

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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.
SETI-0002DIV

SERIAL NO.
10/647,714

Applicant(s): Khan et al.

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